

2SB125 Datasheet, Equivalent, Cross Reference Search

Type Designator: 2SB125

Material of Transistor: Ge

Polarity: PNP

Maximum Collector Power Dissipation (P_c): 41 W

Maximum Collector-Base Voltage $|V_{cb}|$: 36 V

Maximum Emitter-Base Voltage $|V_{eb}|$: 25 V

Maximum Collector Current $|I_c \text{ max}|$: 15 A

Max. Operating Junction Temperature (T_j): 75 °C

Transition Frequency (f_t): 0.18 MHz

Forward Current Transfer Ratio (h_{FE}), MIN: 70

Noise Figure, dB: -

Package: TO53